

ZXTP2029F

100V, SOT23, PNP medium power transistor

Summary

$V_{(BR)CEV} > -130V$, $V_{(BR)CEO} > -100V$

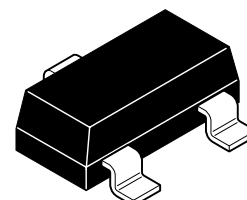
$I_{C(cont)} = -3A$

$R_{CE(sat)} = 45m\Omega$ typical

$V_{CE(sat)} < -80mV$ @ -1A

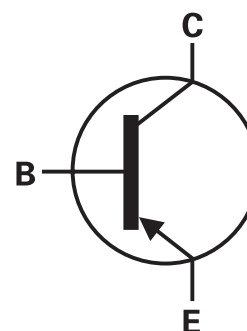
$P_D = 1.2W$

Complementary part number: ZXTN2020F



Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

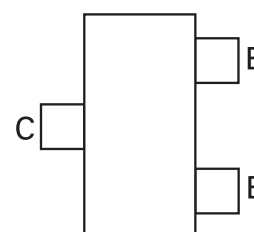


Features

- Higher power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 130V forward blocking voltage

Applications

- MOSFET and IGBT gate driving
- Motor drive
- DC-DC converters
- High side switches



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width	Quantity per reel
ZXTP2029FTA	7	8mm	3,000

Device marking

953

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	-130	V
Collector-emitter voltage	$V_{(BR)CEV}$	-130	V
Collector-emitter voltage	V_{CEO}	-100	V
Emitter-base voltage	V_{EBO}	-7.0	V
Peak pulse current	I_{CM}	-5	A
Continuous collector current ^(a)	I_C	-3	A
Base current	I_B	-1	A
Power dissipation @ $T_A=25^{\circ}\text{C}^{(a)}$	P_D	1.0	W
Linear derating factor		8.0	mW/ $^{\circ}\text{C}$
Power dissipation @ $T_A=25^{\circ}\text{C}^{(b)}$	P_D	1.2	W
Linear derating factor		9.6	mW/ $^{\circ}\text{C}$
Power dissipation @ $T_A=25^{\circ}\text{C}^{(c)}$	P_D	1.56	W
Linear derating factor		12.5	mW/ $^{\circ}\text{C}$
Operating and storage temperature	$T_j; T_{stg}$	-55 to +150	$^{\circ}\text{C}$

Thermal resistance

Parameter	Symbol	Value	Unit
Junction to ambient ^(a)	$R\theta_{JA}$	125	$^{\circ}\text{C}/\text{W}$
Junction to ambient ^(b)	$R\theta_{JA}$	104	$^{\circ}\text{C}/\text{W}$
Junction to ambient ^(c)	$R\theta_{JA}$	80	$^{\circ}\text{C}/\text{W}$

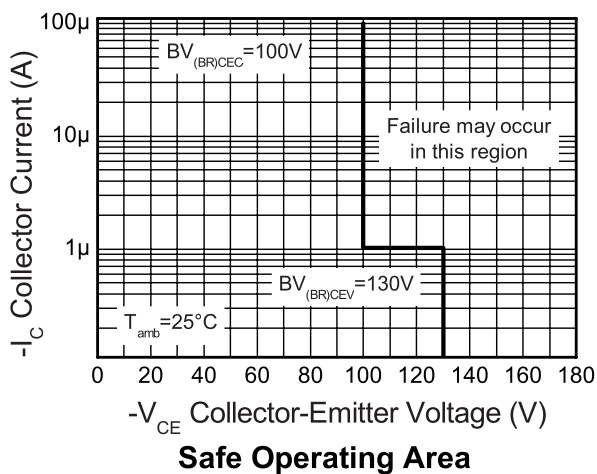
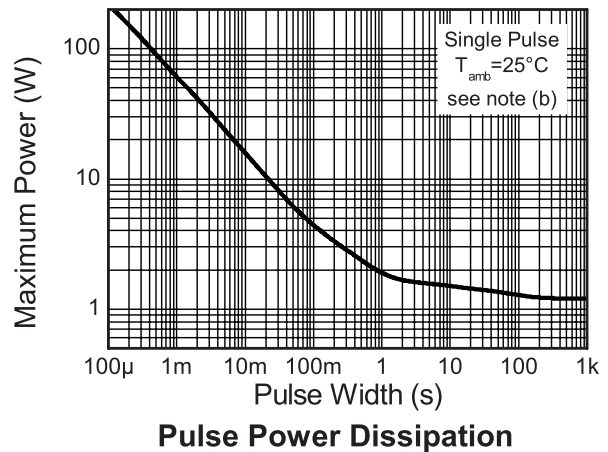
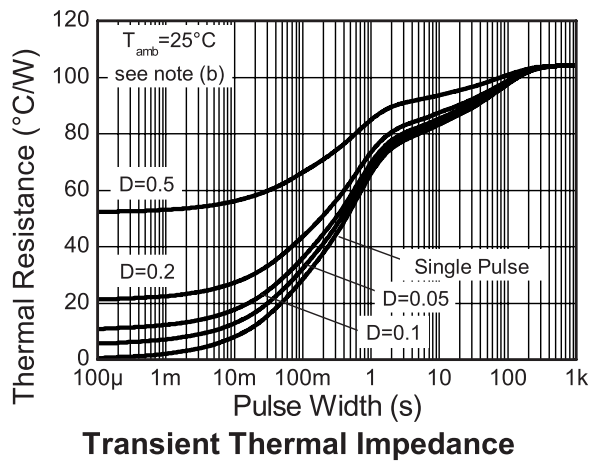
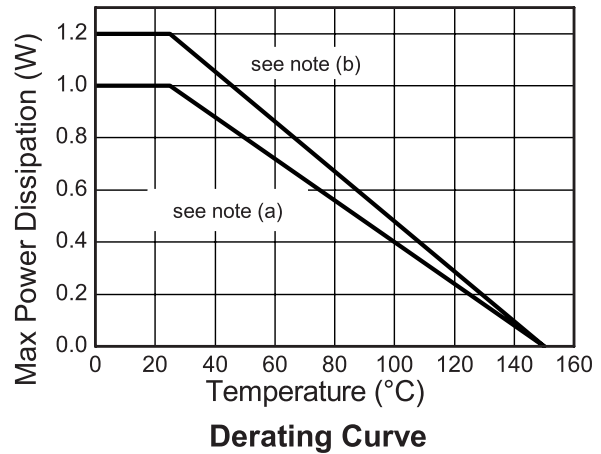
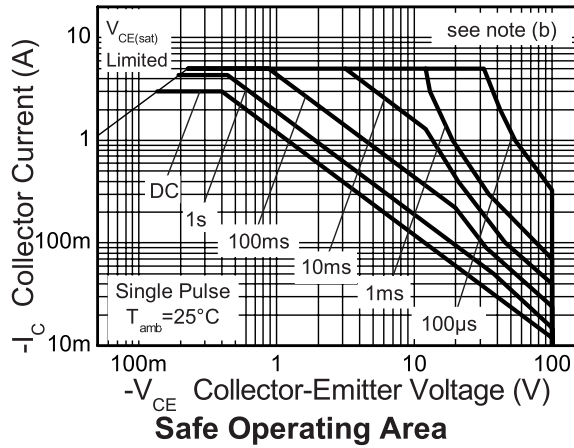
NOTES:

(a) Mounted on 18mm x 18mm x 1.6mm FR4 PCB with a very high coverage of 2 oz weight copper in still air conditions.

(b) Mounted on 30mm x 30mm x 1.6mm FR4 PCB with a very high coverage of 2 oz weight copper in still air conditions.

(c) As (b) above measured at $t < 5\text{secs}$.

Characteristics



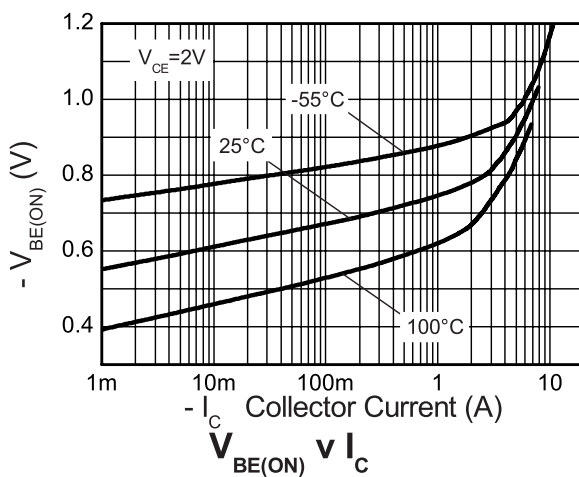
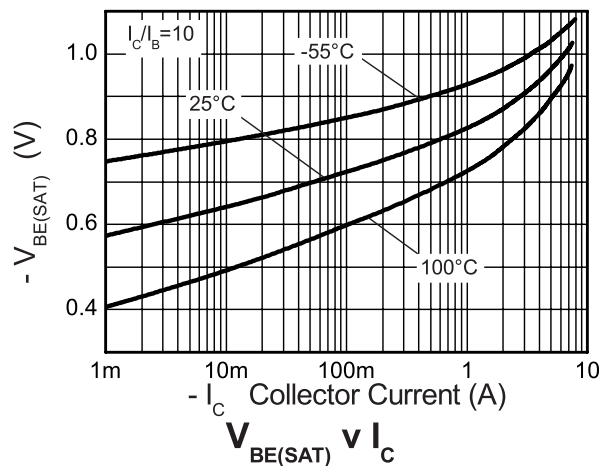
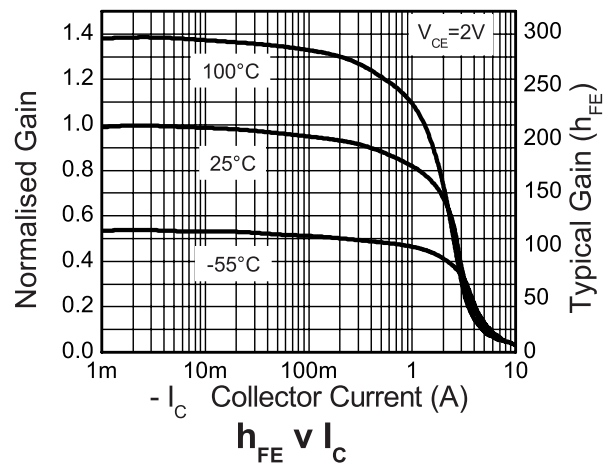
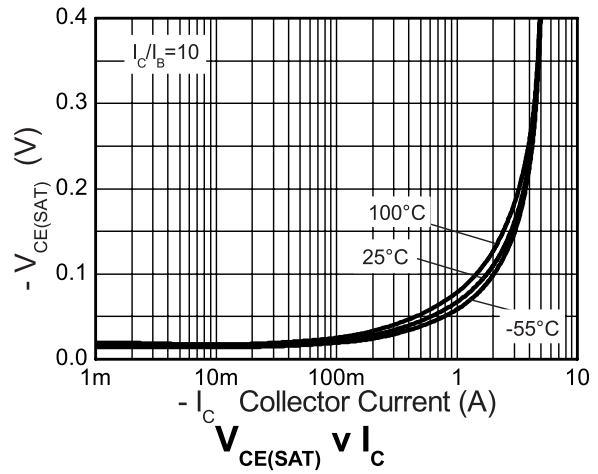
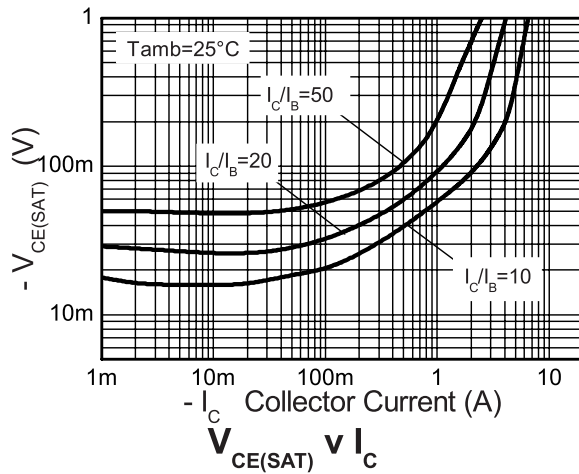
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}$	-130	-160		V	$I_C = -100\mu\text{A}$
Collector-emitter breakdown voltage	$V_{(BR)CEV}$	-130	-160		V	$I_C = -1\mu\text{A}$, $1V > V_{BE} > -0.3V$
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	-100	-120		V	$I_C = -10\text{mA}$ ^(a)
Emitter-base breakdown voltage	$V_{(BR)EBO}$	-7.0	-8.3		V	$I_E = -100\mu\text{A}$
Collector-emitter cut-off current	I_{CEV}			-20	nA	$V_{CE} = -100V$, $V_{BE} = 1V$
Collector-base cut-off current	I_{CBO}			-20	nA	$V_{CB} = -100V$
Emitter-base cut-off current	I_{EBO}			-10	nA	$V_{EB} = -6V$
Static forward current transfer ratio	H_{FE}	100 100 40	220 200 75	300		$I_C = -10\text{mA}$, $V_{CE} = -2V$ ^(a) $I_C = -1A$, $V_{CE} = -2V$ ^(a) $I_C = -3A$, $V_{CE} = -2V$
Collector-emitter saturation voltage	$V_{CE(sat)}$		-20 -60 -135 -180	-30 -80 -180 -250	mV mV mV mV	$I_C = -100\text{mA}$, $I_B = -10\text{mA}$ ^(a) $I_C = -1A$, $I_B = -100\text{mA}$ ^(a) $I_C = -3A$, $I_B = -300\text{mA}$ ^(a) $I_C = -4A$, $I_B = -400\text{mA}$ ^(a)
Base-emitter saturation voltage	$V_{BE(sat)}$		-0.90	-1.00	V	$I_C = -3A$, $I_B = -300\text{mA}$ ^(a)
Base-emitter turn-on voltage	$V_{BE(on)}$		-0.81	-0.90	V	$I_C = -3A$, $V_{CE} = -2V$ ^(a)
Transition frequency	f_T		150		MHz	$I_C = -100\text{mA}$, $V_{CE} = -10V$, $f = 50\text{MHz}$
Output capacitance	C_{obo}		39		pF	$V_{CB} = -10V$, $f = 1\text{MHz}$
Turn-on time	$t_{(on)}$		33		ns	$V_{CC} = -10V$, $I_C = -1A$,
Turn-off time	$t_{(off)}$		344		ns	$I_{B1} = I_{B2} = -100\text{mA}$

NOTES:

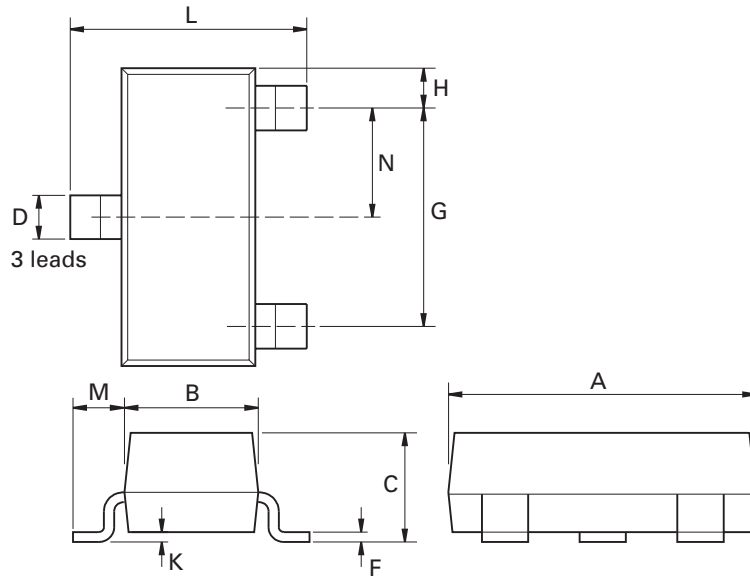
(a) Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$.

Typical characteristics



ZXTP2029F

Packaging details - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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